L Number	Hits	Search Text	DB	Time stamp
1	41	(ferroelectric ferro-electric FeRAM) and	USPAT;	2003/05/19
		(program\$4 writ\$3) and (chang\$3 with polar\$7 with (volt\$3 near3 gate))	US-PGPUB; EPO; JPO; DERWENT;	15:47
2	8	<pre>(ferroelectric ferro-electric FeRAM) and ((program\$4 writ\$3) same (chang\$3 with polar\$7 with (film layer) with (volt\$3 near3 gate)))</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/19 15:48
-	207	(mfs MFMIS) with (ferroelectric ferro-electric)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05
-	109	((mfs MFMIS) with (ferroelectric ferro-electric)) and (writ\$3 program\$4) and (read\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/06 16:59
-	12	<pre>(((mfs MFMIS) with (ferroelectric ferro-electric)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage))</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05 13:58
-	14498	(mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05 13:06
_	3093	((mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)) and (writ\$3 program\$4) and (read\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05 13:08
_	29	<pre>(((mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage))</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/05 12:55
_	18496	(mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/05 13:07
-	3302	((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/05 13:09
_	29	<pre>(((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/06 16:58
-	10	(((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage)) and (ferroelectric adj3 capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:55
-	10	<pre>((((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage)) and (ferroelectric adj3 capacitor)) and (gate adj3 electrode)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:55

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-	4	(((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage)) and ((ferroelectric adj3 capacitor) with (gate adj3 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 17:00
- 10	205	((ferroelectric adj3 capacitor) with (gate adj3 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/06 16:58
-	40	(((ferroelectric adj3 capacitor) with (gate adj3 electrode))) and (mfs MFIS MFMIS)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/06 16:58
-	32	((((ferroelectric adj3 capacitor) with (gate adj3 electrode))) and (mfs MFIS MFMIS)) and (writ\$3 program\$4) and (read\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/06 17:00
-	16	(((((ferroelectric adj3 capacitor) with (gate adj3 electrode))) and (mfs MFIS MFMIS)) and (writ\$3 program\$4) and (read\$3)) and ((ferroelectric ferro-electric) adj3 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/06
-	5690	read\$3 same ((voltage potential bias) with drain with source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:17
-	574	((unsaturat\$3 non-saturat\$3) near3 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:17
-	22	<pre>(((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and (nonvolatile non-volatile)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:19
-	2835	<pre>(read\$3 same ((voltage potential bias) with drain with source)) and (nonvolatile non-volatile)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:20
-	5	<pre>((((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and (nonvolatile non-volatile)) and ((read\$3 same ((voltage potential bias) with drain with source)) and (nonvolatile non-volatile))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:23
_	124614	((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:25
_	22	<pre>(((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and (((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:25
-	1	<pre>((((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and (((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile)) and ((read\$3 with data with (appl\$3 near3 (voltage bias potential)) with source with drain))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:27

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-	1	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:27
1		((read\$3 with data with (appl\$3 near3	EPO; JPO;	
		(voltage bias potential)) with source	DERWENT;	
		with drain))	IBM_TDB	
-	224	(read\$3 with data with (appl\$3 near3	USPAT;	2003/03/20
		(voltage bias potential)) with source	US-PGPUB;	11:30
		with drain)	EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	181	(((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	12:16
		nonvolatile) and ((read\$3 with data with	EPO; JPO;	
		(appl\$3 near3 (voltage bias potential))	DERWENT;	
		with source with drain))	IBM_TDB	
-	1	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:29
		((((MFS MFMIS ferroelectric) near3	EPO; JPO;	
1		transistor) FeRAM non-volatile	DERWENT;	
		nonvolatile) and ((read\$3 with data with	IBM_TDB	
		(appl\$3 near3 (voltage bias potential))]
		with source with drain)))		
-	1669	read\$3 same ((appl\$3 near3 (voltage bias	USPAT;	2003/03/20
		potential)) with source with drain)	US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;]
			IBM_TDB	
-	3	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:45
		(read\$3 same ((appl\$3 near3 (voltage bias	EPO; JPO;	l i
		potential)) with source with drain))	DERWENT;	
			IBM_TDB	·
-	11	((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) with read\$3	US-PGPUB;	11:53
}			EPO; JPO;	ĺ
			DERWENT;	
			IBM_TDB	
-	1	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) with read\$3) and (non-volatile	US-PGPUB;	11:52
		nonvolatile)	EPO; JPO;	l i
	İ		DERWENT;	
			IBM_TDB	
-	3769	(unsaturat\$3 non-saturat\$3) with read\$3	USPAT;	2003/03/20
			US-PGPUB;	11:53
			EPO; JPO;	
			DERWENT;	
l _	3779	/ungatumatés non gatumatés managana (As)	IBM_TDB	2002/02/22
-	3//9	(unsaturat\$3 non-saturat\$3 nonsaturat\$3)	USPAT;	2003/03/20
		with read\$3	US-PGPUB;	11:53
	1		EPO; JPO;	
			DERWENT;	
_	200	((unsaturat\$3 non-saturat\$3 nonsaturat\$3)	IBM_TDB	2002/02/20
} _	200		USPAT;	2003/03/20
]		<pre>with read\$3) and (non-volatile nonvolatile)</pre>	US-PGPUB;	11:54
		nonvoiacite,	EPO; JPO;	
			DERWENT;	į į
<u>_</u>	200	(((MFS MFMIS ferroelectric) near3	IBM_TDB	2003/02/20
	, 200		USPAT;	2003/03/20
		transistor) FeRAM non-volatile nonvolatile) and (((unsaturat\$3	US-PGPUB;	12:04
		non-saturat\$3 nonsaturat\$3) with read\$3)	EPO; JPO;	
		and (non-volatile nonvolatile))	DERWENT; IBM TDB	
_	28	((((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
	20	transistor) FeRAM non-volatile	US-PGPUB;	12:09
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	12:09
ĺ		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
		and (non-volatile nonvolatile))) and	IBM_TDB	
		(read reading)		

-	8	(((((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	12:09
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	
		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
		and (non-volatile nonvolatile))) and	IBM TDB	
		(read reading)) and memory	_	
_	1	((read\$3 with data with (appl\$3 near3	USPAT;	2003/03/20
		(voltage bias potential)) with source	US-PGPUB;	12:19
		with drain)) and ((unsaturat\$3	EPO; JPO;	
		non-saturat\$3 nonsaturat\$3) near3 region)	DERWENT;	
			IBM TDB	
-	1	read\$3 with (unsaturat\$3 non-saturat\$3	USPAT;	2003/03/20
		nonsaturat\$3) with (current near3	US-PGPUB;	12:20
		detect\$3)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	